

## Patent Abstracts of Japan

PUBLICATION NUMBER : 08045926  
PUBLICATION DATE : 16-02-96

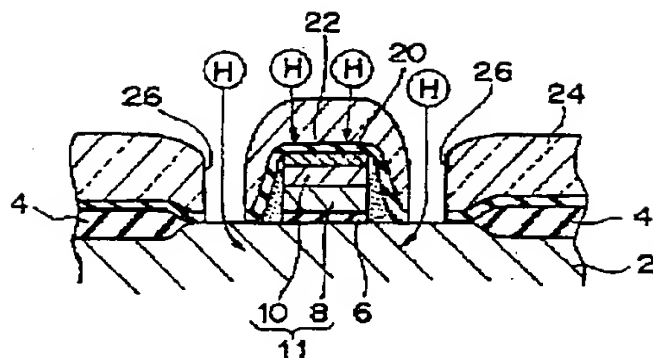
APPLICATION DATE : 26-07-94  
APPLICATION NUMBER : 06174308

APPLICANT : SONY CORP;

INVENTOR : MIZUMURA AKIRA;

INT.CL. : H01L 21/318 H01L 21/027 H01L 21/316

TITLE : SEMICONDUCTOR DEVICE AND ITS  
MANUFACTURE



ABSTRACT : PURPOSE: To enable a transistor to be protected against moisture or phosphorus that penetrates into it through an interlayer film and completely hydrogenated.

CONSTITUTION: A hydrogen supplying source layer 20 which serves as an antireflection layer when a gate electrode 11 is subjected to photolithography processing is provided onto the gate electrode 11 of a transistor. It is preferable that the hydrogen supplying source layer 20 is formed of hydrogen-containing  $\text{SiO}_x\text{N}_y$  film or hydrogen-containing  $\text{Si}_x\text{N}_y$  film. It is preferable that a barrier layer 22 is provided onto the hydrogen supplying source layer 20. It is preferable that the barrier layer 22 is formed of silicon nitride Film prepared through a low-pressure CVD method or an ECR-CVD method. An interlayer film 24 is formed on the barrier layer 22.

COPYRIGHT: (C)1996,JPO